Highly Integrated Wide Bandgap Power Module for Next Generation Plug-In Vehicles

Alex Lednev
General Motors, LLC
04 June 2020
DE-EE0007285

This report was prepared as an account of work sponsored by an agency of the United States Government. Neither the United States Government nor any agency thereof, nor any of their employees, makes any warranty, express or implied, or assumes any legal liability or responsibility for the accuracy, completeness, or usefulness of any information, apparatus, product, or process disclosed, or represents that its use would not infringe privately owned rights. Reference herein to any specific commercial product, process, or service by trade name, trademark, manufacturer, or otherwise does not necessarily constitute or imply its endorsement, recommendation, or favoring by the United States Government or any agency thereof. The views and opinions of authors expressed herein do not necessarily state or reflect those of the United States Government or any agency thereof.



elt082

GENERAL MOTORS

Overview

Timeline

- Start 1 January 2016
- Finish 30 September 2020
- 80% Complete

Funding

- Project Budget \$5.67 million
 \$3.79M Federal Share
 \$1.88M GM Cost Share
- 2019 funds received \$454k
- 2020 funding planned \$501k

Vehicle Technology Barriers

- Lower Cost Electric Drive Systems
- Higher Efficiency, long range EV
- Higher Performance and Lifetime
- Lower Mass and Volume

Project Team

- Lead:
 - General Motors, LLC
- Subrecipients:
 - Virginia Polytechnic Institute and State University
 - Ohio State University
 - Oak Ridge National Lab
 - Monolith Semiconductor, Inc.
- Key Suppliers:
 Wolfspeed (Cree Power)
- Collaborations:
 PowerAmerica

Project Relevance

Research Focus Area: Traction Inverter

- Develop WBG semiconductor based power stage
- Technical development for key components needed for a WBG power stage: design compact gate drive, power module, high voltage capacitor, integrate commercial current sensor, use production ready GM control board, HV motor

Objective

- Automotive power module with SiC MOSFET dies
- Reduce traction inverter and electric motor losses over the drive cycle and quantify efficiency benefits
- Develop technology for long range BEV's with >600V battery
- Implement selected bonding, joining and thermal management solution (low Z_{th} , long lifetime and reliability)

Address DoE Targets

- Enable inverter to meet or exceed DOE 2020 targets:
- Power Density: 13.4kW/l; Specific power: 14.1kW/kg & \$3.3/kW
- Efficiency >94% (10%-100% speed at 20% rated torque)

Uniqueness and Impacts

Compact, high temperature, low inductance automotive package

Milestones

Date	2016-2018 Milestone or Go/No-Go Decisions	Status
June – 2018	Power Module Prototype Perf. – Phase 3 Go/No-Go	Completed
Oct – 2018	Prototype Performance Test Completed - Milestone	Completed
Nov – 2018	Power module and power stage fully characterized	Completed
Dec – 2018	Performed vehicle range study	Completed
Jan – 2020	Rescoped phase III of the project to focus more on electric drive performance and development	Completed
Jan - 2020	Novel gate drive board tested	Completed
Feb - 2020	900V SiC Inverter Build Completed	Completed
Sept – 2019 to Aug – 2020	1200V Module Build	On-Track
Sept – 2019 to Sept – 2020	1200V Inverter Build and Performance Testing	On-Track
Jan – 2020 to Sept – 2020	HV Motor Insulation Study	On-Track

WBG POWER MODULE APPLICATIONS

Features

- Low conduction and switching loss
- Ultra-low parasitic inductances
- High switching frequency operation
- Normally-off device operation
- High temperature operation $T_{i,max} = 175$ °C
- High power high voltage power module

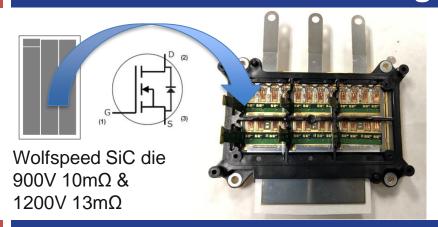
System benefits

- Reduced size and weight
- Compact design and inverter packaging
- High efficiency inverter
- Increased power density
- Improved thermal performance and packaging

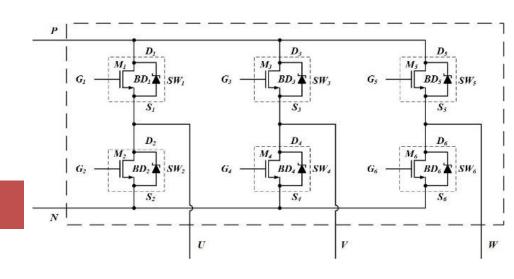
Potential applications

- High efficiency converters
 Such as dc/dc boost converter
- Traction power inverters

SiC Power Module Package



Functional Circuit



Technical Approach

- This program will develop a highly integrated wide band gap automotive power module with a smaller package, lower mass and higher efficiency
- Targets higher DC link bus voltage systems (e.g. $600-800V_{DC}$) and maximum phase currents of $300-500A_{RMS}$
- The high power density module utilizes SiC MOSFET die to enable high efficiency operation
- Higher power density will be further enabled through the removal of the external diode by using the third quadrant operational capability of the SiC MOSFET
- Design a package that has low stray inductance
 - Target below 10nH for the complete power stage
 - Design power module with stray inductance below 5nH
- Develop advanced current sensing methods
- Develop short circuit protection methods



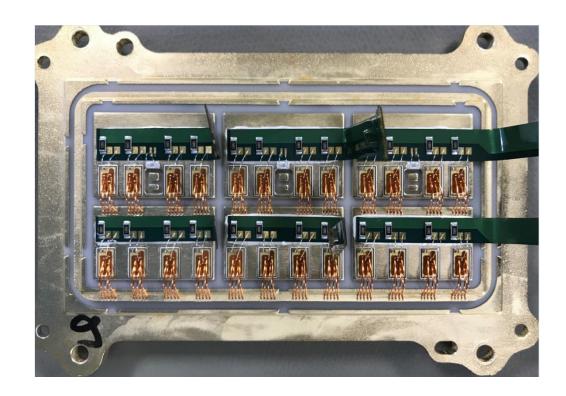
Accomplishments: Inverter with 900V SiC Die Complete

- Inverter with 900V SiC die successfully completed
- 900V SiC power modules successfully passed characterization and performance tests
- Successful leak test and high potential test (2200V)
- Package is the same as the 1200V SiC inverter that is currently under development



Accomplishments: 1200V SiC Die and Substrates

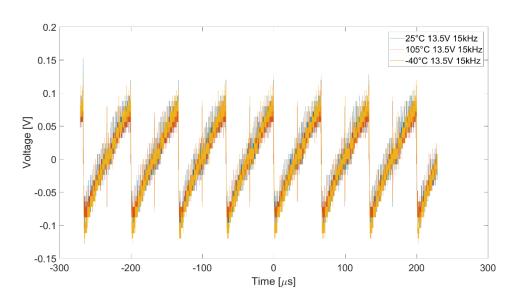
- 12 prototype substrates built with 1200V SiC Die
- 4 substrates fully functional without any problems
- Redesigned die top system (DTS) to account for new die layout
- Aluminum wirebond size increased and attachment points adjusted
- Thermistor added to the 1200V SiC modules



- New tool developed for flexible PCB cable assembly process to increase yield
- Next steps are to complete the power module builds and assemble full inverters

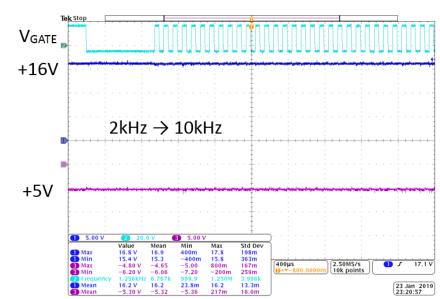
Accomplishments:

Novel, Compact Gate Drive Board with Very Tight Voltage Regulation



 The gate bias supply is designed to remain extremely stable under quickly changing load conditions, showing almost no voltage change transitioning from 2kHz to 10kHz switching

- The gate bias supply is designed to provide a very reliable gate voltage (+/-150mV) across all temperatures from -40 to 150°C
- This tight voltage regulation enables the selection of precise gate bias voltages, improving performance and efficiency

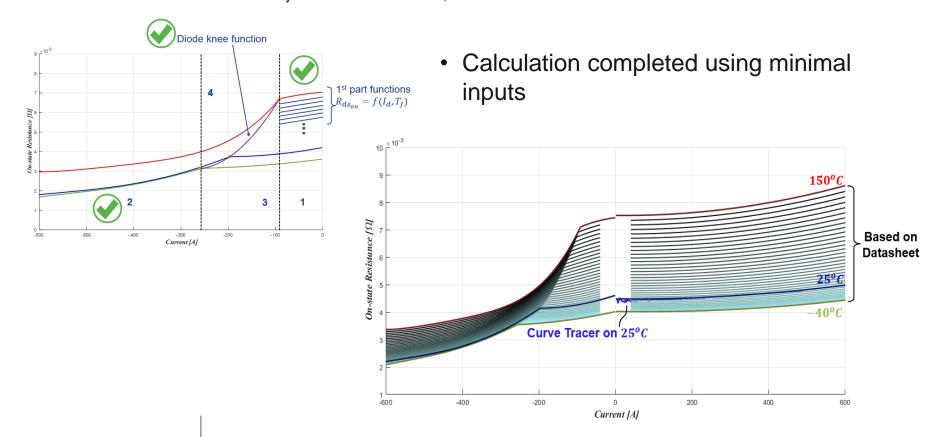




Accomplishments:

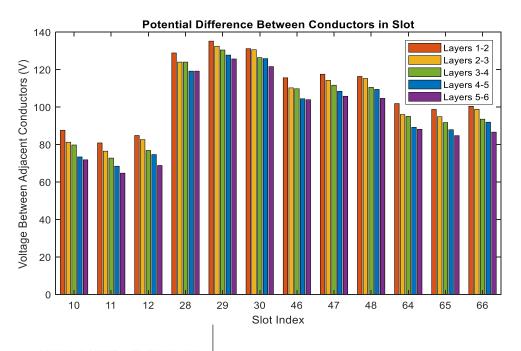
R_{ds,on}-Based T_j Estimation

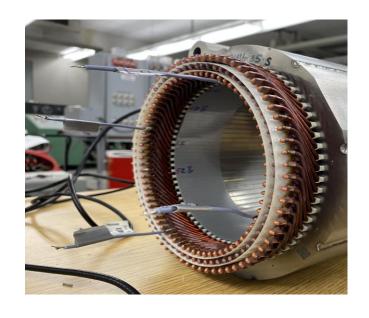
• Developed an algorithm and physical method to calculate individual device junction temperature, T_i, based on R_{ds,on} measured during device operation



Accomplishments: 24-Turn HV Motor Simulation & Test

- Developed a two dimensional simulation of a 24 turn motor
- Calculated the voltage differences between conductors in different slots





- Simulation results verified by real motor testing
- Next steps are to understand dv/dt and insulation impacts of the HV motor

GENERAL MOTORS

Remaining Challenges, Barriers & Future Plans

Challenges & Potential Barriers

- Power module yield during prototype construction
- HV capacitor availability due to COVID-19 impact
- Development of high bandwidth low cost current sensing
- Gate drive improvements: design reliable and fast short circuit protection that is integrated and faster than standard "de-sat" protection
- EMI noise generation due to the high dv/dt switching
- Electric motor insulation (increased dv/dt)
- Inverter cost is increased due to the high cost of SiC die

Future Plans (FY2020)

- Construction and testing of power module with 1200V SiC die
- Test electric drive system on dyne
- HV motor study



Summary

- Complete inverter successfully built and passed leak and high potential (2200V) tests (SiC MOSFETs 900V, 2.5mOhm)
- Gate drive solution completed and built
- HV capacitor developed
- Complete power stage package is about 60% of the standard Si power stage
- T_j estimation algorithm has been developed based on limited inputs
- HV motor study has commenced and preliminary simulation results align with HV motor lab testing
- Project is in final budget period fabrication & inverter level testing on dyne (new substrates with 1200V, 13mOhm die have

been successfully manufactured)